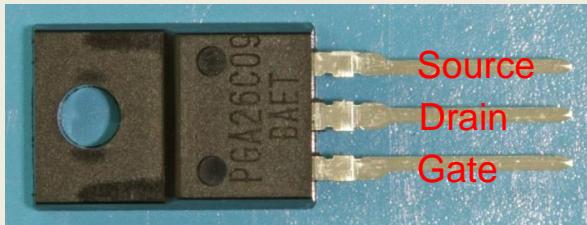
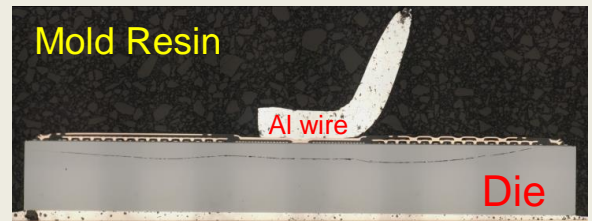


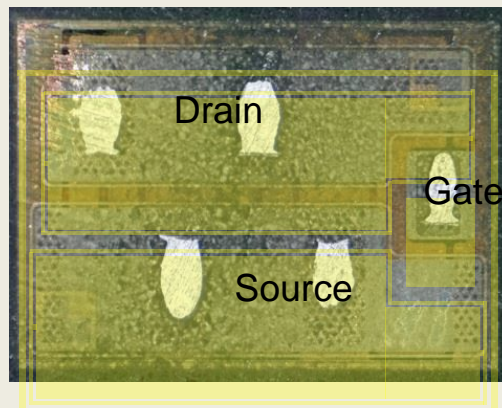
**PANASONIC PGA26C09 DV GaN POWER SEMICONDUCTOR DEVICE  
DETAILED STRUCTURE ANALYSIS REPORT**



**TO-220 Package**



**Cross-section**



**GaN Die**

This 89 page report reveals construction details of the Panasonic PGA26C09DV GaN power semiconductor device including two-layer Cu interconnect, Al bond wire over active area, on-chip integrated Gate ESD protection, and unique recessed/regrowth AlGaN channel barrier structure.

The report includes package details, layout analysis, die analysis by delayering, cross-sections (SEM, TEM), and materials analysis (EDX).

**Priced to sell at \$5,000**

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